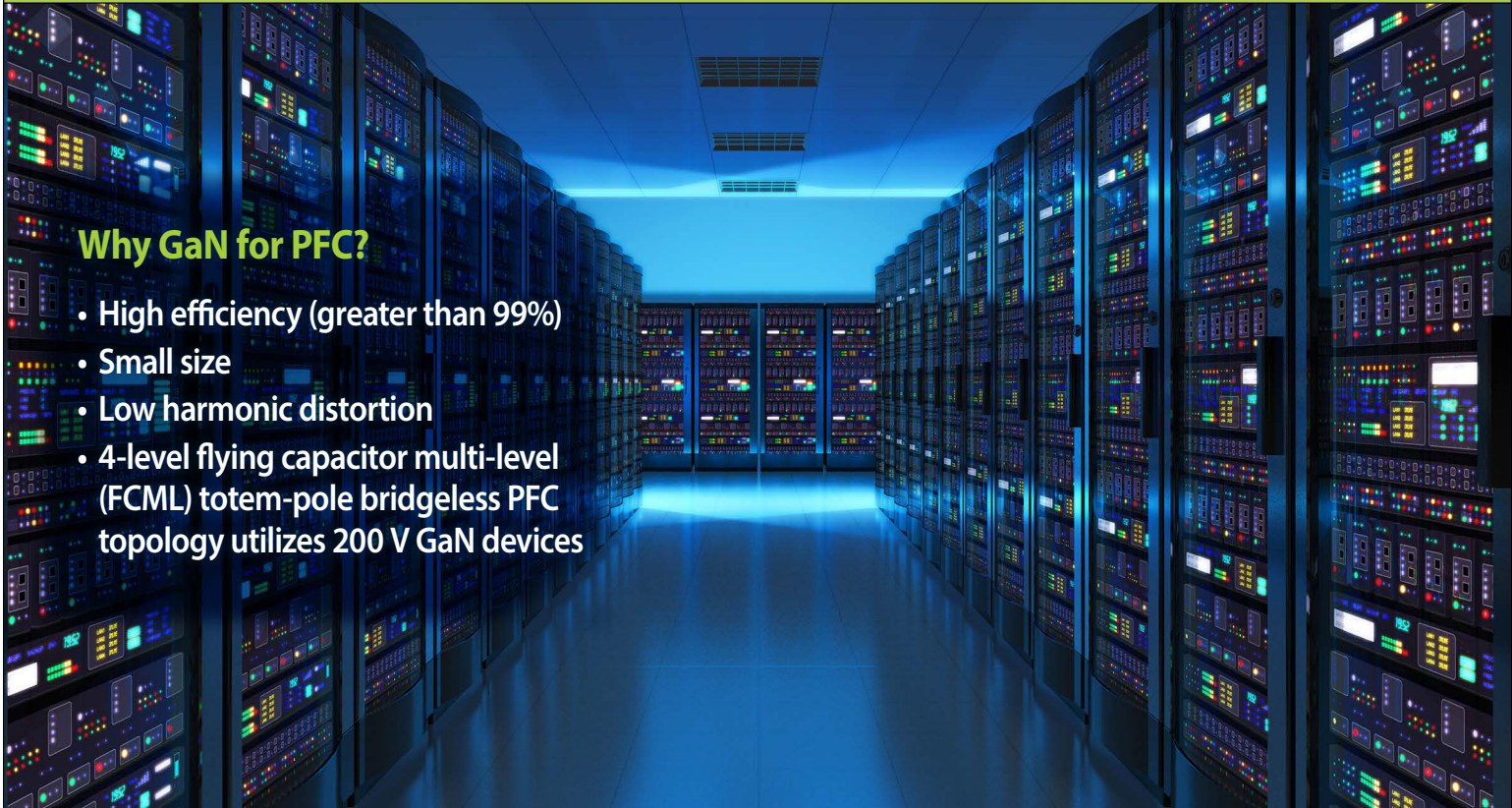
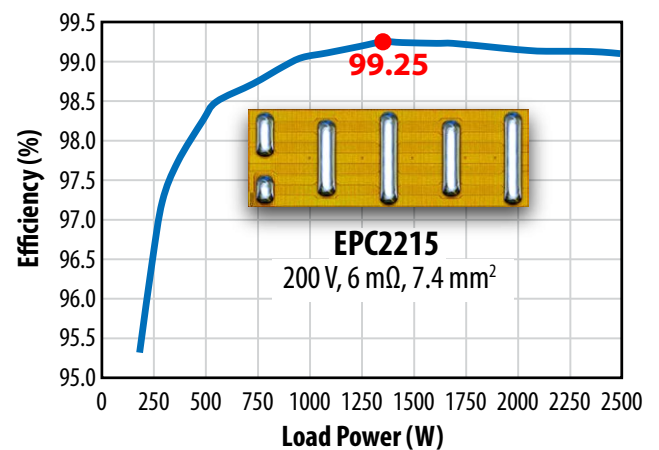
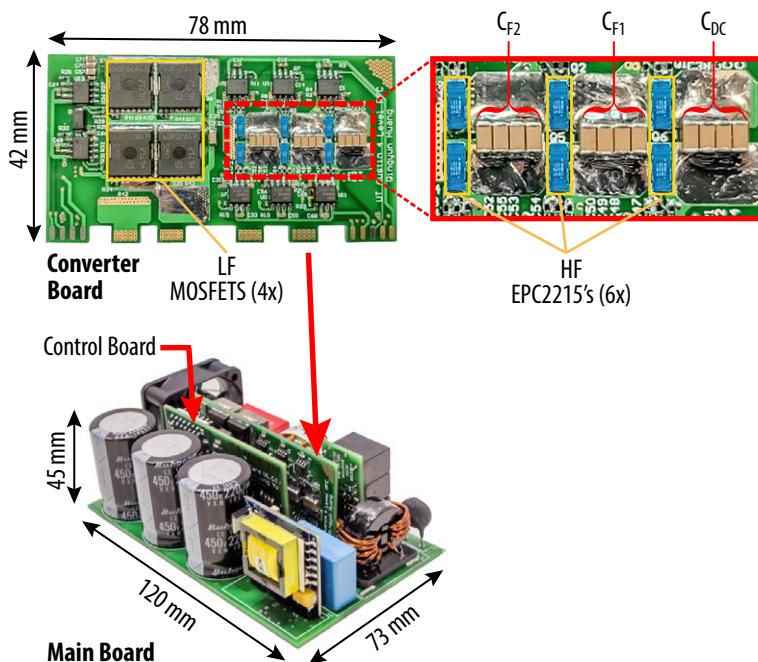


eGaN® FETs and ICs for 1 kW – 3 kW Universal Input Power Factor Correction (PFC)

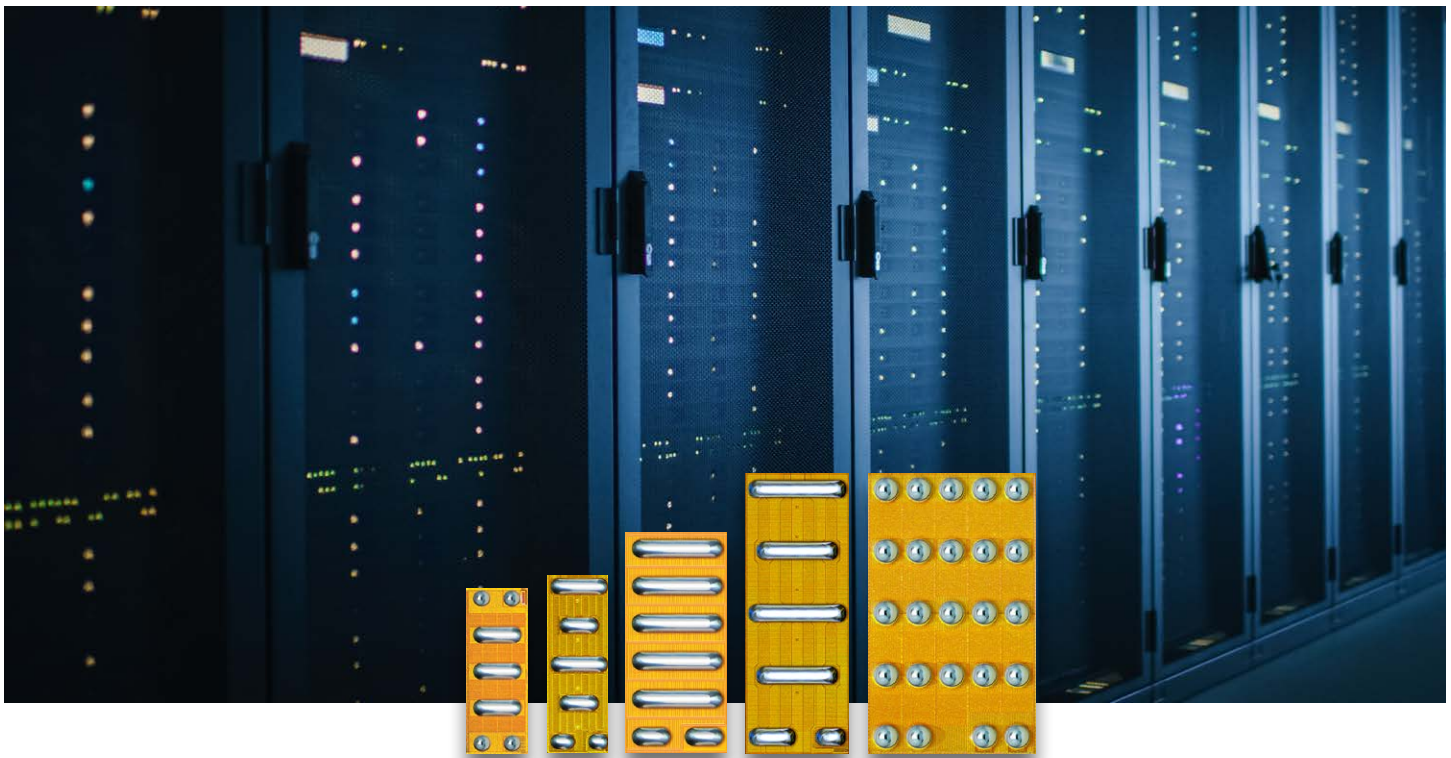


Why GaN for PFC?

- High efficiency (greater than 99%)
- Small size
- Low harmonic distortion
- 4-level flying capacitor multi-level (FCML) totem-pole bridgeless PFC topology utilizes 200 V GaN devices



Reference Design	V _{IN}	V _{OUT}	Power Level	Featured Product
Universal input 4-Level totem-pole PFC	85 V _{AC} – 264 V _{AC}	400 _{DC}	2.5 kW	EPC2215



Part Number	Configuration	V _{DS}	Max R _{DS(on)} (mΩ) @ 5V _{GS}	Q _G typ (nC)	Q _{GS} typ (nC)	Q _{GD} typ (nC)	Q _{OSS} typ (nC)	Q _{RR} (nC)	I _D (A)	Pulsed I _D (A)	Package (mm)	Half Bridge Development Board
EPC2019	Single	200	50	1.8	0.6	0.35	18	0	8.5	42	LGA 2.77 x 0.95	EPC9014
EPC2010C	Single	200	25	3.7	1.3	0.7	40	0	22	90	LGA 3.6 x 1.6	EPC9003C
EPC2207	Single	200	22	4.5	1.3	0.7	23	0	14	54	LGA 2.9 x 0.9	EPC90124
EPC2215	Single	200	8	13.6	3.3	2.1	69	0	32	162	LGA 4.6 x 1.6	EPC9099
EPC2034C	Single	200	8	11.4	3.8	2.1	95	0	48	213	BGA 4.6 x 2.6	EPC9048C

Table data subject to change. Please refer to the Product section on www.epc.com

Design Support Materials @ www.epc-co.com

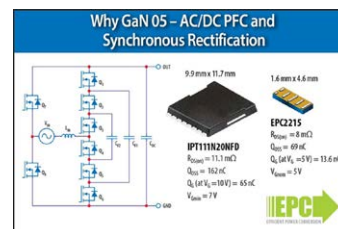


Books

GaN Transistors for Efficient Power Conversion

Videos

Why GaN for AC/DC PFC and Synchronous Rectification



Application Note

How to Design a Highly Efficient, 2.5 kW, Universal Input Voltage Range, Power Factor Correction (PFC) 400 V Rectifier Using 200 V eGaN® FETs



For More Information

Please contact info@epc-co.com or your local sales representative
 Visit our website: epc-co.com
 Sign-up to receive EPC updates at bit.ly/EPcupdates



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